

AUTOMOTIVE CURRENT TRANSDUCER OPEN LOOP TECHNOLOGY HAH1DRW 1200-S/SP1





Introduction

The HAH1DRW family is for the electronic measurement of DC, AC or pulsed currents in high power and low voltage automotive applications with galvanic separation between the primary circuit (high power) and the secondary circuit (electronic circuit).

The HAH1DRW family gives you the choice of having different current measuring ranges in the same housing.

Features

- Ratiometric transducer
- Open Loop transducer using the Hall effect
- Low voltage application
- Unipolar +5 V DC power supply
- Primary current measuring range ±1200 A
- Maximum RMS primary admissible current: defined by busbar to have T < +150 °C
- Operating temperature range: −40 °C < T < 125 °C
- Output voltage: full ratio-metric (in sensitivity and offset).

Special feature

· Connector MQS type from TE.

Advantages

- Excellent accuracy
- Very good linearity
- Very low thermal offset drift
- · Very low thermal sensitivity drift
- Galvanic separation
- High frequency bandwidth
- Non intrusive solution.

Automotive applications

- Electrical Power Steering
- Starter Generators
- Converters
- Battery Management
- Motor drive application.

Principle of HAH1DRW Family

The open loop transducers uses a Hall effect integrated circuit. The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current I_p to be measured.

The current to be measured $I_{\rm P}$ is supplied by a current source i.e. battery or generator (Figure 1).

Within the linear region of the hysteresis cycle, ${\it B}$ is proportional to:

$$B\left(I_{\mathsf{P}}\right) = a \times I_{\mathsf{P}}$$

The Hall voltage is thus expressed by:

$$U_{\mathsf{H}} = (c_{\mathsf{H}}/d) \times I_{\mathsf{H}} \times a \times I_{\mathsf{P}}$$

Except for $I_{\rm p}$, all terms of this equation are constant. Therefore:

$$U_{\rm H} = b \times I_{\rm p}$$
 a constant
 b constant
 $c_{\rm H}$ Hall coefficient
 d thickness of the Hall plate
 $I_{\rm H}$ current across the Hall plates

The measurement signal $\,U_{\rm H}$ amplified to supply the user output voltage or current.

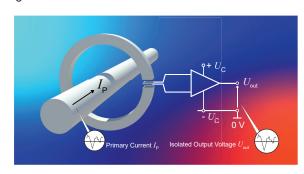
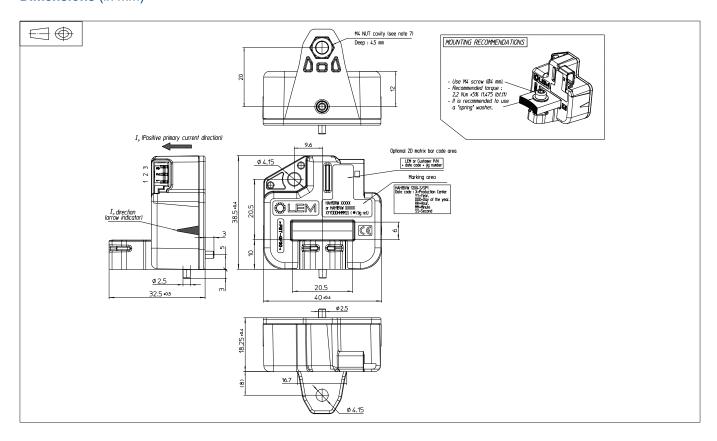


Fig. 1: Principle of the open loop transducer.



Dimensions (in mm)

HAH1DRW1200-S/SP1



Mechanical characteristics

Plastic case
 PBT GF30

Magnetic core
 FeSi wound core

• Mass 57 g ±5 %

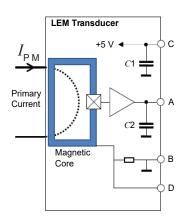
Pins
 Brass tin plated

• IP level IPx2.

Mounting recommendation

• Assembly torque max 2.2 N·m ±5 %

Electronic schematic



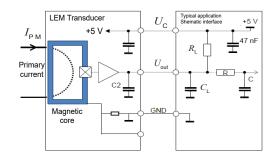
	Components list					
IC	Hall sensor ASIC					
C1	Decoupling capacitor	47 nF				
C2	C2 EMC protection capacitor					
	Pin out					

	Pin out
1	U _c (+5 V)
2	Ground
3	U_{out}

Remark

• $U_{\text{out}} > U_{\text{o}}$ when I_{P} flows in the positive direction (see arrow on drawing).

System architecture (example)



 $C_{\rm L}$ < 2.2 nF EMC protection (optional) *RC* Low pass filter (optional)

On board diagnostic

 $R_{\rm I}$ > 10 k Ω . Resistor for signal line diagnostic (optional)

$U_{ m out}$	Diagnostic
Open circuit	$U_{\rm IN} = U_{\rm C}$
Short GND	U _{IN} = 0 V



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Absolute ratings (not operating)

Parameter	Symbol	Unit	Specification			Conditions	
Parameter			Min	Typical	Max	Conditions	
Maximum supply voltage	$U_{\rm C\; max}$	V	-0.5		8	1)	
Ambient storage temperature	$T_{\rm S}$	°C	-40		125		
Electrostatic discharge voltage (HBM)	U_{ESDHBM}	kV			8		
Maximum admissible vibration (random RMS)	γ_{max}	m·s⁻²			96.6	10 to 2000 Hz, -40 °C to 125 °C	
RMS voltage for AC insulation test	$U_{\rm d}$	kV			2.5	50 Hz, 1 min	
Creepage distance	d_{Cp}	mm	4.85				
Clearance	d_{CI}	mm	4.85				
Comparative tracking index	CTI		PLC3				
Maximum output current	$I_{ m out\; max}$	mA	-10		10		
Maximum output voltage	$U_{ m outmax}$	V	-0.5		U _c + 0.5		

Operating characteristics in nominal range ($I_{\rm P\,N}$)

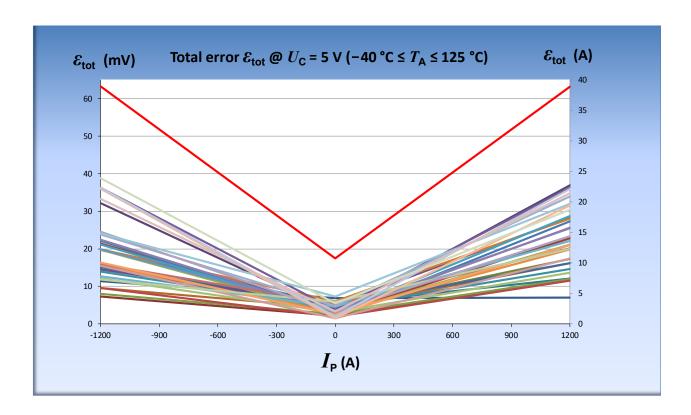
Parameter	Cumbal	Unit	Specification			Conditions	
Parameter	Symbol		Min	Typical	Max	Conditions	
Electrical Data							
Primary current, measuring range	I_{PM}	Α	-1200		1200		
Primary nominal RMS current	I_{PN}	Α	-1200		1200		
Supply voltage	U_{C}	V	4.75	5	5.25		
Ambient operating temperature	T_{A}	°C	-40 125		125		
Output voltage (Analog)	U_{out}	V	$U_{\text{out}} = ($	$U_{\rm c}/5) \times (U_{\rm c}$	$+ S \times I_{P}$)		
Sensitivity	S	mV/A		1.67		@ T _A = 25 °C	
Offset voltage	U_{o}	V		2.5			
Current consumption	I_{C}	mA		20	25		
Load resistance	R_{L}	ΚΩ	10				
Output internal resistance	$R_{ m out}$	Ω		1	10		
		Perfo	ormance	Data			
Ratiometricity error	$\varepsilon_{\rm r}$	%		±0.5		@ T _A = 25 °C	
Sensitivity error	ε_{s}	%		±0.7		$\textcircled{@}\ T_{\text{A}}$ = 25 °C, $\textcircled{@}\ U_{\text{C}}$ = 5 V	
Electrical offset voltage	U_{OE}	mV		±3		@ $T_{\rm A}$ = 25 °C, @ $U_{\rm C}$ = 5 V	
Magnetic offset voltage	U_{OM}	mV		±2		$\textcircled{0}$ U_{C} = 5 V, $\textcircled{0}$ T_{A} = 25 °C	
Linearity error	$\varepsilon_{_{\!\!L}}$	%	-1		1	% of full scale	
Average temperature coefficient of $U_{\mathrm{O}\mathrm{E}}$	$TCU_{ extsf{OEAV}}$	mV/°C		±0.05		@ U _C = 5 V	
Average temperature coefficient of S	TCS _{AV}	%/°C		±0.02			
Delay time to 90 % of I _{PN}	t _{D 90}	μs		2	6	$di/dt = 100 \text{ A/}\mu\text{s}$	
Frequency bandwidth	BW	kHz	40			@ -3 dB	
Peak-to-peak noise voltage	$U_{\rm nopp}$	mV			14	DC to 1 MHz	
Output RMS voltage noise	U_{no}	mV			2.2		
Phase shift	Δφ	۰	-4			DC to 1 KHz	

 $\underline{\text{Note}}$: Exceeding 6.5 V may temporarily reconfigure the device until next power on.





Total error $\varepsilon_{\mbox{\tiny tot}}$



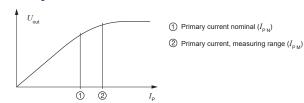
	Total error $arepsilon_{ ext{tot}}$ specification								
$I_{P}\left(A\right)$	T_{A} =	25 °C, $U_{\rm c}$ =	5 V	-40 °C ≤ $T_{\rm A}$ ≤125 °C, $U_{\rm C}$ =5 V					
-1200	45 mV	27 A	2.25 %	65 mV	39 A	3.25 %			
0	13 mV	7.8 A	0.65 %	18 mV	10.8 A	0.90 %			
1200	45 mV	27 A	2.25 %	65 mV	39 A	3.25 %			



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PERFORMANCES PARAMETERS DEFINITIONS

Primary current definition:



Definition of typical, minimum and maximum values:

Minimum and maximum values for specified limiting and safety conditions have to be understood as such as values shown in "typical" graphs. On the other hand, measured values are part of a statistical distribution that can be specified by an interval with upper and lower limits and a probability for measured values to lie within this interval. Unless otherwise stated (e.g. "100 % tested"), the LEM definition for such intervals designated with "min" and "max" is that the probability for values of samples to lie in this interval is 99.73 %. For a normal (Gaussian) distribution, this corresponds to an interval between -3 sigma and +3 sigma. If "typical" values are not obviously mean or average values, those values are defined to delimit intervals with a probability of 68.27 %, corresponding to an interval between -sigma and +sigma for a normal distribution. Typical, minimum and maximum values are determined during the initial characterization of a product.

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear amplifier.

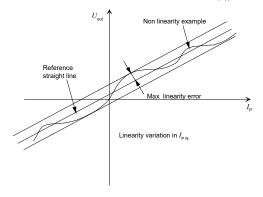
Magnetic offset:

The magnetic offset is the consequence of an any current on the primary side. It's defined after a stated excursion of primary current.

Linearity:

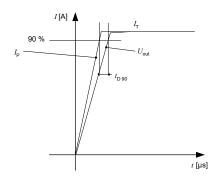
The maximum positive or negative discrepancy with a reference straight line $U_{\rm out}$ = $f(I_{\rm p})$.

Unit: linearity (%) expressed with full scale of I_{PN} .



Delay time $t_{D 90}$:

The time between the primary current signal $(I_{\rm P\ N})$ and the output signal reach at 90 % of its final value.



Sensitivity:

The transducer's sensitivity S is the slope of the straight line $U_{\text{out}} = f(I_{\text{p}})$, it must establish the relation:

$$U_{\text{out}}(I_{\text{P}}) = U_{\text{C}}/5 (S \times I_{\text{P}} + U_{\text{O}})$$

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25 $^{\circ}$ C.

The offset variation $I_{\text{O }T}$ is a maximum variation the offset in the temperature range:

$$I_{\text{O}\,\text{T}} = I_{\text{O}\,\text{E}} \max - I_{\text{O}\,\text{E}} \min$$

The offset drift $TCI_{\rm O~E~AV}$ is the $I_{\rm O~T}$ value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25 $^{\circ}$ C.

The sensitivity variation S_{τ} is the maximum variation (in ppm or %) of the sensitivity in the temperature range: S_{τ} = (Sensitivity max – Sensitivity min) / Sensitivity at 25 °C.

The sensitivity drift TCS_{AV} is the S_{τ} value divided by the temperature range. Deeper and detailed info available is our LEM technical sales offices (www.lem.com).

Offset voltage @ $I_p = 0$ A:

The offset voltage is the output voltage when the primary current is zero. The ideal value of $U_{\rm O}$ is $U_{\rm C}/2$. So, the difference of $U_{\rm O}-U_{\rm C}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis. Deeper and detailed info available is our LEM technical sales offices (www.lem. com).

Environmental test specifications:

Refer to LEM GROUP test plan laboratory CO.11.11.515.0 with "Tracking_Test Plan_Auto" sheet.



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Standard				
N @ 25 °C (initial)				
LEM 98.20.00.574.0				
LEM 98.20.00.573.0				
LEM 98.20.00.370.0				
LEM 98.20.00.579.0				
N WITH T °C (initial)				
LEM 98.20.00.574.0				
LEM 98.20.00.574.0				
LEM 98.20.00.573.0				
LEM 98.20.00.573.0				
LEM 98.20.00.370.0				
LEM 98.20.00.579.0				
ESTS @ 25 °C				
100 Hz to 10 kHz @ 20 A peak				
Sweep from DC to 1 MHz				
100 A/μs. <i>I</i> pulse = 700				
2000 V/µs. <i>U</i> = 2000 V				
2500 V AC / 1 min / 50 Hz				
500 V DC, time = 60 s R_{INS} ≥ 500 MΩ Minimum				
TESTS (CLIMATIC)				
IEC 60068-2-14 Na (01/2009)				
JESD 22-A101 (03/2009)				
AL TESTS				
IEC 60068-2-64 (02/2008)				
IEC 60068-2-27 (02/2008)				
IEC 60068-2-31 §5.2: method 1 (05/2008)				
G				
ISO 10605 (07/2008)				
ISO 11452-4 (12/2011)				
CISPR 25 (03/2008)				
CTERIZATION				